

Resonant Switching Series

Reverse conducting IGBT with monolithic body diode

IHW30N110R3

Data sheet

Industrial Power Control

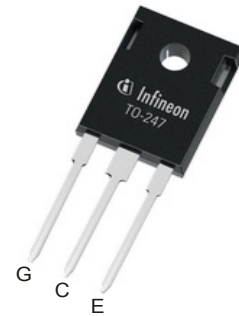
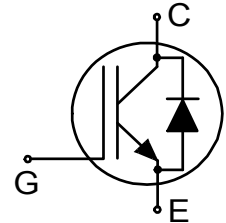
Reverse conducting IGBT with monolithic body diode

Features:

- Powerful monolithic body diode with low forward voltage designed for soft commutation only
- Very tight parameter distribution
- High ruggedness, temperature stable behavior
- Low V_{CEsat}
- Easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
- Low EMI
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>

Applications:

- Inductive cooking
- Inverterized microwave ovens
- Resonant converters
- Soft switching applications



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
IHW30N110R3	1100V	30A	1.55V	175°C	H30R1103	PG-TO247-3